

600V N-Channel Power MOSFET

Features

- $R_{DS(ON)}$ <2.4 Ω @ V_{GS} =10V
- Fast switching capability
- Lead free in compliance with EU RoHS directive.
- Green molding compound

PRODUCT	SUMMARY

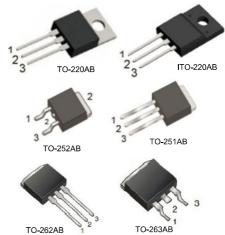
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)
600	2.4 @ V _{GS} =10V	4

Mechanical Data

 Case: TO-251AB,TO-252AB,TO-220,ITO-220AB TO-262AB,TO-263AB Package

Ordering Information

Part No.	Package	Packing
AU4N60S	TO-251AB	75pcs / Tube
AD4N60S	TO-252AB	2.5Kpcs / 13" Reel
AT4N60S	TO-220AB	50pcs / Tube
AF4N60S	ITO-220AB	50pcs / Tube
AK4N60S	TO-262AB	50pcs / Tube
AG4N60S	TO-263AB	800pcs / 13" Reel
-		



Pin Definition:

- 1. Gate
- 2. Drain
- 3. Source

Block Diagram



ABSOLUTE MAXIMUM RATINGS (T_C=25°C, unless otherwise specified)

a.				
PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	600	٧
Gate-Source Voltage		V_{GSS}	±30	V
Continuous Drain Curre	ent	I _D	4.0	Α
Pulsed Drain Current (I	Note 2)	I _{DM}	16	Α
Avalanche Energy	Single Pulsed (Note 3)	E _{AS}	217	mJ
	TO-220AB/TO-262AB/TO-263AB		106	W
Power Dissipation	ITO-220AB	P_{D}	44	W
	TO-251AB/TO-252AB		77	W
Junction Temperature		TJ	+150	°C
Operating Temperature		T_OPR	-55 ~ +150	°C
Storage Temperature		T_{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

- 2. Repetitive Rating: Pulse width limited by maximum junction temperature
- 3. L = 30mH, I_{AS} = 3.7A, V_{DD} = 50V, R_{G} = 25 Ω , Starting T_{J} = 25°C

Document ID	Issued Date	Revised Date	Revision	Page.
AS-3150050	2003/03/08	2012/05/16	D	9



600V N-Channel Power MOSFET

THERMAL DATA

PARAMETER		SYMBOL	RATING	UNIT
Junction to Ambient	TO-220AB/ITO-220AB TO-262AB/TO-263AB	$ heta_{JA}$	62.5	°C/W
	TO-251AB/TO-252AB	ŬJA .	110	
	TO-220AB TO-262AB/TO-263AB		2.35	
Junction to Case	ITO-220AB	θ_{JC}	5.5	°C/W
	TO-251AB/TO-252AB		2.9	

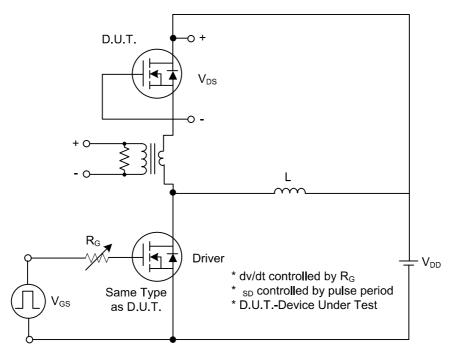
ELECTRICAL CHARACTERISTICS (T_C=25°C, unless otherwise specified)

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS				•	•		
Drain-Source Breakdown Voltage)	BV _{DSS}	$V_{GS} = 0V, I_D = 250\mu A$	600			V
Drain-Source Leakage Current		I _{DSS}	V _{DS} = 600V, V _{GS} = 0V			1	μΑ
Gate-Source Leakage Current	Forward Reverse	I _{GSS}	$V_{GS} = 30V, V_{DS} = 0V$ $V_{GS} = -30V, V_{DS} = 0V$			100 -100	nA nA
ON CHARACTERISTICS	•		7 50	•	•	•	
Gate Threshold Voltage		$V_{GS(TH)}$	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2.0		4.0	V
Static Drain-Source On-State Res	sistance	R _{DS(ON)}	$V_{GS} = 10V, I_D = 2.0A$		1.9	2.4	Ω
DYNAMIC CHARACTERISTICS							
Input Capacitance		C _{ISS}			550		pF
Output Capacitance		Coss	V _{DS} = 25V, V _{GS} = 0V, f = 1MHz		80		pF
Reverse Transfer Capacitance		C _{RSS}			30		pF
SWITCHING CHARACTERISTIC	S	_			-		
Turn-On Delay Time		t _{D(ON)}			35		ns
Turn-On Rise Time		t _R	V _{DD} = 300V, I _D = 4.0A,		80		ns
Turn-Off Delay Time		t _{D(OFF)}	R _G = 25Ω (Note 1, 2)		160		ns
Turn-Off Fall Time		t _F			120		ns
Total Gate Charge		Q_G	V _{DS} = 480V,I _D = 4.0A,		80		nC
Gate-Source Charge		Q_GS	V _{DS} = 460V,I _D = 4.0A, -V _{GS} = 10V (Note 1, 2)		5		nC
Gate-Drain Charge		Q_GD	V _{GS} = 10V (Note 1, 2)		20		nC
SOURCE- DRAIN DIODE RATIN	IGS AND CI	HARACTERIS	ŢICS				
Drain-Source Diode Forward Volt	age	V_{SD}	V_{GS} =0V, I_{S} =4A			1.4	V
Maximum Continuous Drain-Sour Forward Current	ce Diode	I s				4	Α
Maximum Pulsed Drain-Source Description Forward Current	iode	I _{SM}				16	Α
Reverse Recovery Time		t _{rr}	$V_{GS} = 0 \text{ V}, I_{S} = 4A,$		400		ns
Reverse Recovery Charge		Q _{RR}	dI _F /dt = 100 A/ μs (Note 1)		1.7		μC
Notes: 1 Pulse Test: Pulse width	4000 B						

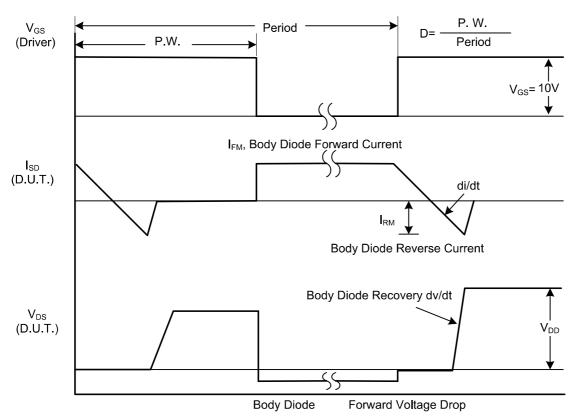
Notes: 1. Pulse Test: Pulse width≤300µs, Duty cycle≤2%

2. Essenti ly independent of operating temperature

TEST CIRCUITS AND WAVEFORMS



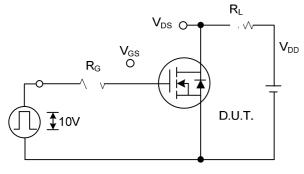
Peak Diode Recovery dv/dt Test Circuit



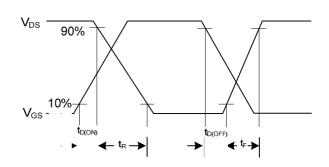
Peak Diode Recovery dv/dt Waveforms

600V N-Channel Power MOSFET

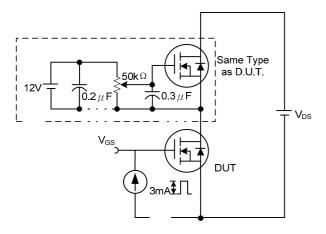
TEST CIRCUITS AND WAVEFORMS(Cont.)



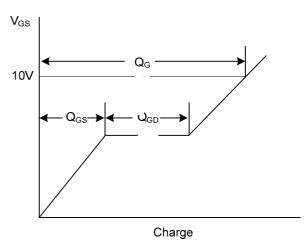
Switching Test Circuit



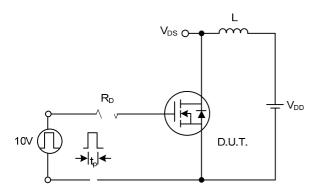
Switching Waveforms



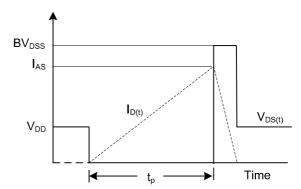
Gate Charge Test Circuit



Gate Charge Waveform



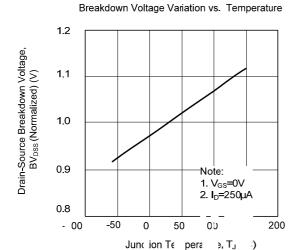
Unclamped Inductive Switching Test Circuit

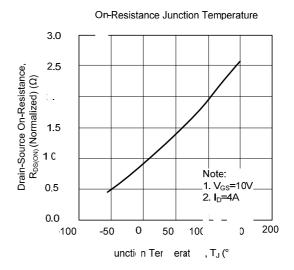


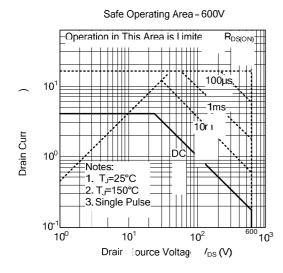
Unclamped Inductive Switching Waveforms

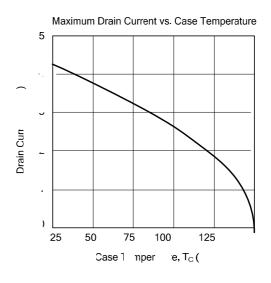
600V N-Channel Power MOSFET

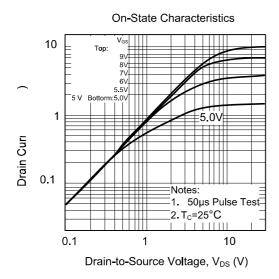
TYPICAL CHARACTERISTICS

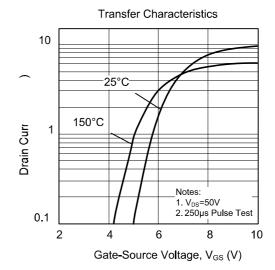






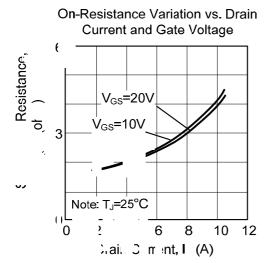


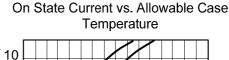


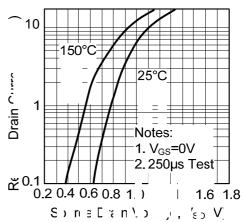


600V N-Channel Power MOSFET

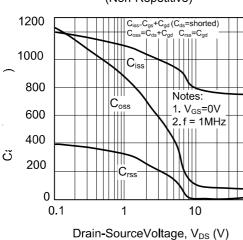
TYPICAL CHARACTERISTICS(Cont.)



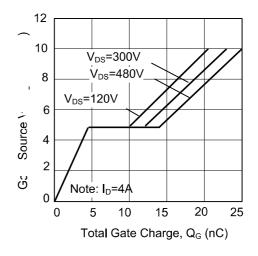




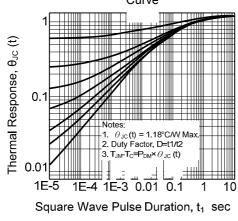


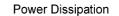


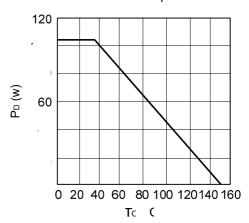
Gate Charge Characteristics



Transient Thermal Response Curve







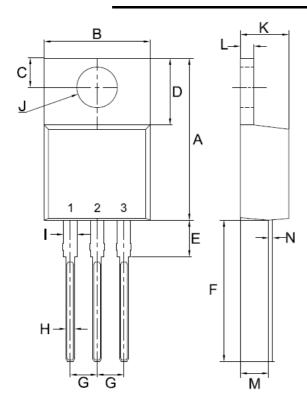


Document ID	Issued Date	Revised Date	Revision	Page.
AS-3150050	2003/03/08	2012/05/16	D	9



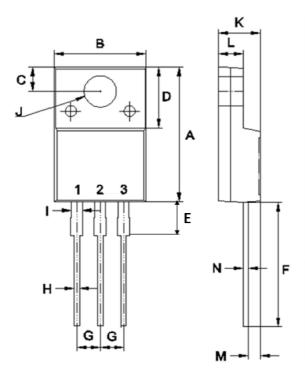
600V N-Channel Power MOSFET

TO-220AB Mechanical Drawing



	TO-220AB			
	Unit:m	m		
DIM	MIN	MAX		
A	14. 80	15. 80		
В	9. 57	10. 57		
С	2. 54	2. 94		
D	5. 80	6. 80		
Е	2. 95	3. 95		
F	12.70	13. 40		
G	2. 34	2.74		
Н	0.51	1. 11		
Ι	0. 97	1. 57		
J	3. 54 ø	4. 14 ø		
K	4. 27	4. 87		
L	1. 07	1. 47		
M	2. 03	2. 92		
N	0.30	0.64		

ITO-220AB Mechanical Drawing

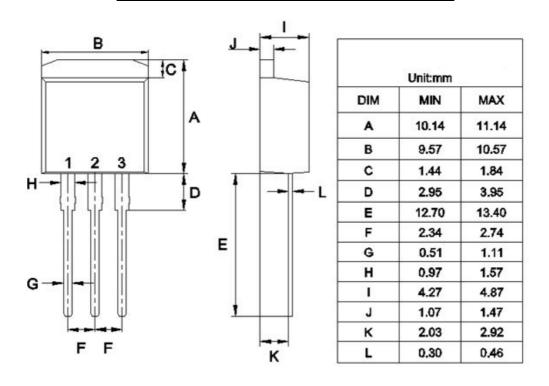


ITO-220AB Unitmm				
DIM	MIN	MAX		
A	14.50	15.50		
В	9.50	10.50		
С	2.50	2.90		
Δ	6.30	7.30		
E	3.30	4.30		
F	13.00	14.00		
G	2.35	2.75		
H	0.30	0.90		
Ι	0.90	1.50		
J	3.20	3.80		
K	4.24	4.84		
L	2.52	2.92		
М	1.09	1.49		
N	0.47	0.64		

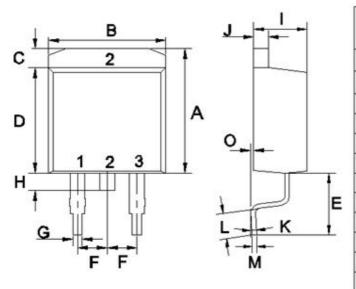


600V N-Channel Power MOSFET

TO-262AB Mechanical Drawing



TO-263AB Mechanical Drawing

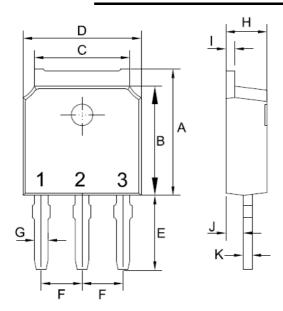


DIM	MIN	MAX
A	10.44	10.84
В	9.81	10. 21
C	1.44	1.84
D	8. 80	9. 20
E	4. 46	4.66
F	2. 44	2.64
G	0.61	1.01
H	0.70	1. 30
I	4. 27	4.87
J	1.07	1.47
K	0°	8°
L	2. 10	2. 50
M	0.30	0.46
0	0	0. 25



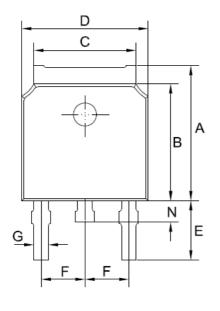
600V N-Channel Power MOSFET

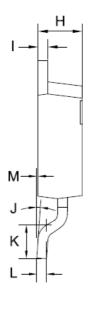
TO-251AB Mechanical Drawing



	Unit:mm	
DIM	MIN	MAX
A	6.85	7. 25
В	5. 90	6.30
С	5. 13	5. 53
D	6.40	6.80
Е	3. 95	4.35
F	2. 19	2. 39
G	0.45	0.85
Н	2. 20	2.40
Ι	0.41	0.61
J	0.71	1.31
K	0.41	0.61

TO-252AB Mechanical Drawing





Unit:mm		
DIM	MIN	MAX
A	6.85	7. 25
В	5. 90	6.30
С	5. 13	5. 53
D	6.40	6.80
E	2.90	3.30
F	2. 19	2.39
G	0.45	0.85
Н	2. 20	2.40
I	0.41	0.61
J	0°	8°
K	1.45	1.85
L	0.41	0.61
М	0.00	0.12
N	0.60	1.00

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for MOSFET category:

Click to view products by AnBon manufacturer:

Other Similar products are found below:

614233C 648584F FDPF9N50NZ IRFD120 IRFF430 JANTX2N5237 2N7000 FCA20N60_F109 FDZ595PZ 2SK2267(Q) 2SK2545(Q,T)
405094E 423220D MIC4420CM-TR VN1206L 614234A 715780A SSM6J414TU,LF(T 751625C PSMN4R2-30MLD

TK31J60W5,S1VQ(O 2SK2614(TE16L1,Q) DMN1017UCP3-7 EFC2J004NUZTDG FCAB21350L1 P85W28HP2F-7071 DMN1053UCP4-7

NTE2384 NTE2969 NTE6400A DMN61D9UWQ-13 US6M2GTR DMN31D5UDJ-7 SSM6P54TU,LF DMP22D4UFO-7B

IPS60R3K4CEAKMA1 DMN1006UCA6-7 DMN16M9UCA6-7 STF5N65M6 STU5N65M6 C3M0021120D DMN13M9UCA6-7

BSS340NWH6327XTSA1 MCM3400A-TP DMTH10H4M6SPS-13 IPS60R1K0PFD7SAKMA1 IPS60R360PFD7SAKMA1

IPS60R600PFD7SAKMA1 IPS60R210PFD7SAKMA1 DMN2990UFB-7B